

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-20	V	
Gate-Source Voltage			V_{GSS}	±8	V
Drain Current (Note 5)	Steady State	$T_A = +25$ °C $T_A = +85$ °C	I _D	-430 -310	mA
Pulsed Drain Current (Note 6)			I _{DM}	-750	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	230	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	558	°C/W
Total Power Dissipation (Note 6)		P_{D}	320	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	393	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

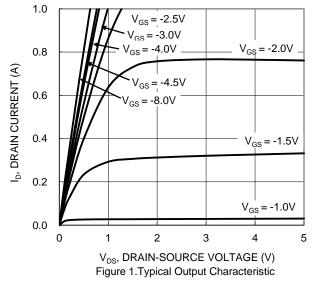
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

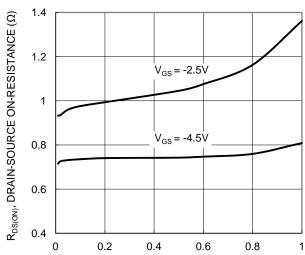
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1.0	μΑ	V _{DS} = -20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±1.0	μА	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	0.7	1.1	Ω	$V_{GS} = -4.5V$, $I_D = -430mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}		1.0	1.6		$V_{GS} = -2.5V, I_D = -300mA$	
			1.3	2.4		$V_{GS} = -1.8V, I_D = -150mA$	
Diode Forward Voltage	V_{SD}	_	-0.8	-1.4	V	$V_{GS} = 0V, I_{S} = -115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C_{iss}	1	47	_	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss		6.8	_	pF		
Reverse Transfer Capacitance	C_{rss}	1	4.9	_	pF		
Gate Resistance	R_{g}		240	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$	
Total Gate Charge V _{GS} = -4.5V	Q_g	_	0.55	_	nC	V _{DS} = -10V, I _D = -250mA	
Total Gate Charge V _{GS} = -8V	Qg	_	0.97	_	nC		
Gate-Source Charge	Q_{gs}	_	0.05	_	nC		
Gate-Drain Charge	Q_{gd}	_	0.1	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.9	_	ns		
Turn-On Rise Time	t _R		3.3	_	ns	$V_{DD} = -3V, V_{GS} = -2.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	25.5	_	ns	$R_G = 25\Omega$, $I_D = -100$ mA	
Turn-Off Fall Time	t _F	_	19.3		ns		
Reverse Recovery Time	t _{RR}	_	7.3	_	ns	I _F =-1A, di/dt=-100A/μs	
Reverse Recovery Charge	Q_{RR}	_	1.9	_	nC	I _F =-1A, di/dt=-100A/μs	

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

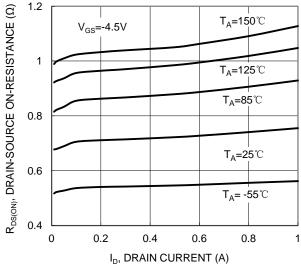


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

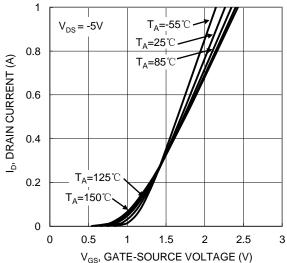
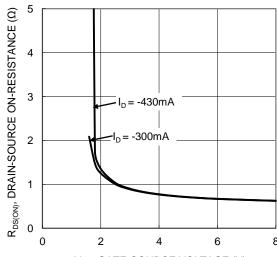


Figure 2. Typical Transfer Characteristic



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

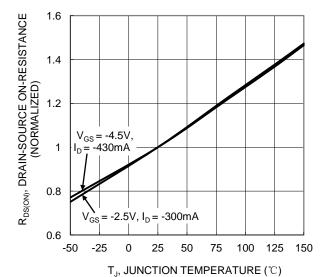
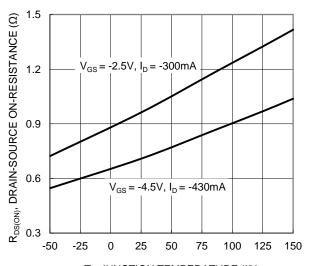


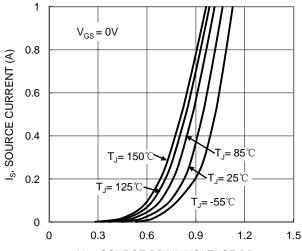
Figure 6. On-Resistance Variation with Temperature



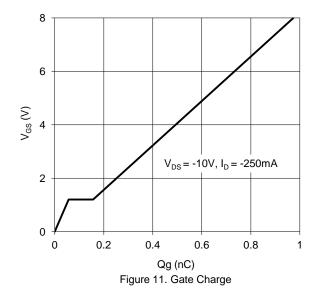


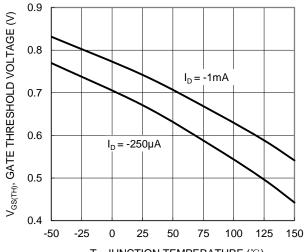


 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C) Figure 7. On-Resistance Variation with Temperature

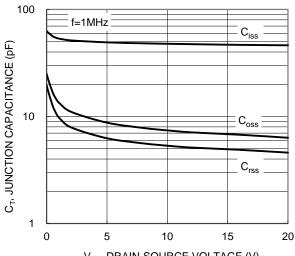


V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current





 T_J , JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. JunctionTemperature



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance

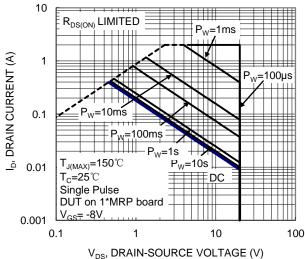


Figure 12. SOA, Safe Operation Area



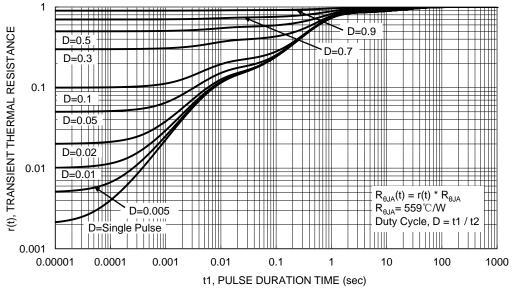
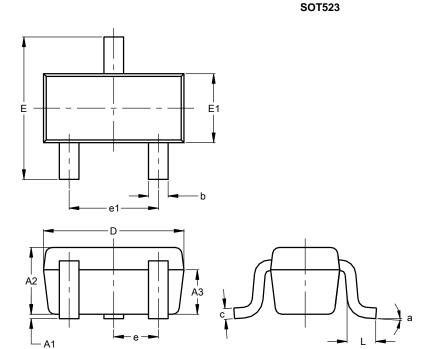


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



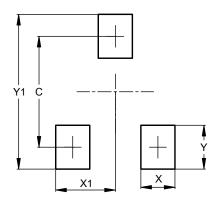
	SOT523					
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.60	0.80	0.75			
А3	0.45	0.65	0.50			
b	0.15	0.30	0.22			
С	0.10	0.20	0.12			
D	1.50	1.70	1.60			
Е	1.45	1.75	1.60			
E1	0.75	0.85	0.80			
е	0.50 BSC					
e1	0.90	1.10	1.00			
L	0.20	0.40	0.33			
а	0°		8°			
All Dimensions in mm						



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)		
С	1.29		
Х	0.40		
X1	0.70		
Y	0.51		
Y1	1.80		

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